

## DESCRIPTION

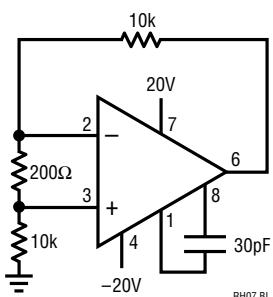
The RH07 is a precision op amp which provides very low offset voltage, low drift and low noise. In the design, processing and testing of the device, particular attention has been paid to the optimization of the entire distribution of several key parameters. The wafer lots are processed to LTC's in-house Class S flow to yield circuits usable in stringent military applications.

For complete electrical specifications, performance curves, application notes and applications circuits, see the OP-07 data sheet.

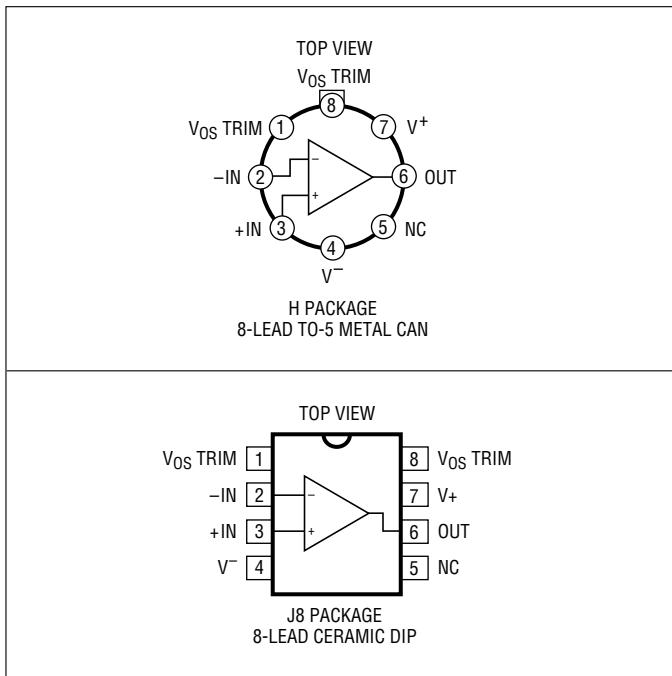
## ABSOLUTE MAXIMUM RATINGS

Supply Voltage .....	±22V
Differential Input Voltage .....	±30V
Input Voltage .....	±22V
Output Short-Circuit Duration (Note 3) .....	Indefinite
Operating Temperature Range .....	-55°C to 125°C
Storage Temperature Range .....	-65°C to 150°C
Lead Temperature (Soldering, 10 sec) .....	300°C

## BURN-IN CIRCUIT



## PACKAGE INFORMATION



**TABLE 1: ELECTRICAL CHARACTERISTICS** (Pre-Irradiation) (Note 5)

SYMBOL	PARAMETER	CONDITIONS	NOTES	T <sub>A</sub> = 25°C			SUB-GROUP	−55°C ≤ T <sub>A</sub> ≤ 125°C			SUB-GROUP	UNITS
				MIN	TYP	MAX		MIN	TYP	MAX		
V <sub>OS</sub>	Input Offset Voltage		1		75	4			200		2,3	μV
ΔV <sub>OS</sub>	Avg Input Offset Voltage Drift:											
ΔTemp	Without External Trim		3							1.3		μV/°C
	With External Trim	Null Pot = 20kΩ	3							1.3		μV/°C
ΔV <sub>OS</sub>	Long-Term Input Offset		2,3		1							μV/Mo
ΔTime	Voltage Stability											
I <sub>OS</sub>	Input Offset Current				2.8	1			5.6		2,3	nA
ΔI <sub>OS</sub>	Avg Input Bias Current Drift		3						50			pA/°C
I <sub>B</sub>	Input Bias Current				±3	1			±6		2,3	nA
ΔI <sub>B</sub>	Avg Input Bias Current Drift		3						50			pA/°C
e <sub>n</sub>	Input Noise Voltage	0.1Hz to 10Hz	3		0.6							μV <sub>P-P</sub>
	Input Noise Voltage Density	f <sub>0</sub> = 10Hz	4		18							nV/√Hz
		f <sub>0</sub> = 100Hz	3		13							nV/√Hz
		f <sub>0</sub> = 1000Hz	3		11							nV/√Hz
i <sub>n</sub>	Input Noise Current	0.1Hz to 10Hz	3		30							pA <sub>P-P</sub>
	Input Noise Current Density	f <sub>0</sub> = 10Hz	3		0.80							pA/√Hz
		f <sub>0</sub> = 100Hz	3		0.23							pA/√Hz
		f <sub>0</sub> = 1000Hz	3		0.17							pA/√Hz
R <sub>IN</sub>	Input Resistance: Differential Mode Common Mode		3	20		200						MΩ GΩ
	Input Voltage Range		3	±13.5				±13.5				V
CMRR	Common-Mode Rejection Ratio	V <sub>CM</sub> = ±13V		110			1	106			2,3	dB
PSRR	Power Supply Rejection Ratio	V <sub>S</sub> = ±3V to ±18V		100			1	94			2,3	dB
A <sub>VOL</sub>	Large-Signal Voltage Gain	R <sub>L</sub> ≥ 2k, V <sub>O</sub> = ±10V R <sub>L</sub> ≥ 500Ω, V <sub>O</sub> = ±0.5V V <sub>S</sub> = ±3V	3	200 150			4	150			5,6	V/mV V/mV
V <sub>OUT</sub>	Maximum Output Voltage Swing	R <sub>L</sub> ≥ 10k R <sub>L</sub> ≥ 2k R <sub>L</sub> ≥ 1k			±12.5 ±12.0 ±10.5		4 4 4		±12.0		5,6	
SR	Slew Rate	R <sub>L</sub> ≥ 2k	3	0.1								V/μs
GBW	Closed-Loop Bandwidth	A <sub>VCL</sub> = 1	3	0.4								MHz
P <sub>D</sub>	Power Dissipation	V <sub>S</sub> = ±15V V <sub>S</sub> = ±3V			120 6	1						mW mW

**TABLE 1A: ELECTRICAL CHARACTERISTICS** (Post-Irradiation) (Note 6)

SYMBOL	PARAMETER	CONDITIONS	NOTES	10KRAD(Si) MIN MAX	20KRAD(Si) MIN MAX	50KRAD(Si) MIN MAX	100KRAD(Si) MIN MAX	200KRAD(Si) MIN MAX	UNITS
$V_{OS}$	Input Offset Voltage		1	90	150	200	250	300	$\mu\text{V}$
$I_{OS}$	Input Offset Current			2.8	4	8	12	20	nA
$I_B$	Input Bias Current			$\pm 3$	$\pm 10$	$\pm 25$	$\pm 50$	$\pm 100$	nA
	Input Voltage Range		3	$\pm 13.5$	$\pm 13.5$	$\pm 13.5$	$\pm 13.5$	$\pm 13.5$	V
CMRR	Common-Mode Rejection Ratio	$V_{CM} = \pm 13\text{V}$		110	110	105	100	95	dB
PSRR	Power Supply Rejection Ratio	$V_S = \pm 3\text{V}$ to $\pm 18\text{V}$		100	100	100	95	90	dB
$A_{VOL}$	Large-Signal Voltage Gain	$R_L \geq 2\text{k}$ , $V_0 = \pm 10\text{V}$		200	200	180	150	120	$\text{V}/\text{mV}$
$V_{OUT}$	Maximum Output Voltage Swing	$R_L \geq 10\text{k}$		$\pm 12.5$	$\pm 12.5$	$\pm 12.5$	$\pm 12.5$	$\pm 12.5$	V
SR	Slew Rate	$R_L \geq 2\text{k}$		0.1	0.1	0.1	0.075	0.05	$\text{V}/\mu\text{s}$
$P_D$	Power Dissipation			120	120	120	120	120	mW

**Note 1:** Offset voltage is measured with high speed test equipment approximately 0.5 seconds after power is applied.

**Note 2:** Long-term input offset voltage stability refers to the averaged trend line of  $V_{OS}$  vs. time over extended periods after the first 30 days of operation. Excluding the initial hour of operation, changes in  $V_{OS}$  during the first 30 days are typically  $2.5\mu\text{V}$ .

**Note 3:** Parameter is guaranteed by design, characterization, or correlation to other tested parameters.

**Note 4:** 10Hz noise voltage density is sample tested on every lot to an LTPD of 15. Devices 100% tested at 10Hz are available on request.

**Note 5:**  $V_S = \pm 15\text{V}$ ,  $V_{CM} = 0\text{V}$ , unless otherwise noted.

**Note 6:**  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 15\text{V}$ ,  $V_{CM} = 0\text{V}$ , unless otherwise noted.

**TABLE 2: ELECTRICAL TEST REQUIREMENTS**

MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
Final Electrical Test Requirements (Method 5004)	1*,2,3,4,5,6
Group A Test Requirements (Method 5005)	1,2,3,4,5,6
Group B and D for Class S, and Group C and D for Class B	1
End Point Electrical Parameters (Method 5005)	

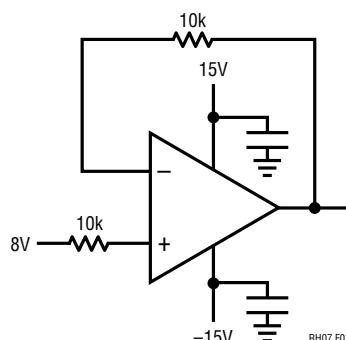
\* PDA Applies to subgroup 1. See PDA Test Notes.

#### PDA Test Notes

The PDA is specified as 5% based on failures from group A, subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883 Class B. The verified failures of group A, subgroup 1, after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent for the lot.

Linear Technology Corporation reserves the right to test to tighter limits than those given.

## TOTAL DOSE BIAS CURRENT



RH07 F01

## TYPICAL PERFORMANCE CHARACTERISTICS

